## **Supplementary Information for**

## Modulation effect of S vacancy and Mo edge on the adsorption and dissociation behaviors of toxic gas (H<sub>2</sub>S, SO<sub>2</sub>) molecules on MoS<sub>2</sub> monolayer

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Figure S1. Spin-polarized band structures for (a)  $H_2S$ , (b) tilted structure, and (c) end-on structure of SO<sub>2</sub> adsorbed on MoS<sub>2</sub> with SV and (d)  $H_2S$ , (e) tilted structure, and (f) end-on structure of SO<sub>2</sub> adsorbed on Mo edge.



Figure S2.Calculted spin-polarized band structure and total density of states (TDOS) for the dissociated configuration of  $H_2S$  on  $MoS_2$  with S vacancy.



**Figure S3.** Top view (upper panel) and side view (lower panel) of optimized structure of O and S-O group adsorbed at Mo-50 edge, which is energetically unfavored by 1.25 eV related to the geometry of SO<sub>2</sub> molecule physisorbed at Mo-50 edge shown in Fig.4(b).



**Figure S4. (a)** Top view (upper panel) and side view (lower panel) of optimized structure of H-Mo-50 edge.



**Table S1**. Calculated formation energy  $(E_f)$  of single S vacancy of pristine MoS<sub>2</sub> ML and edge S vacancy of Mo-50 edge. The formation energy is calculated as  $E_f = E_{SV} + V_S - E_0$ , where  $E_{SV}$ ,  $E_S$  and  $E_0$  are calculated total energies for MoS<sub>2</sub> with SV or Mo-50 edge with edge SV, isolated S atom and clean MoS<sub>2</sub> ML or Mo-50 edge, respectively.

|           | MoS <sub>2</sub> ML | Mo-50 edge |
|-----------|---------------------|------------|
| $E_f(eV)$ | 6.65                | 5.01       |